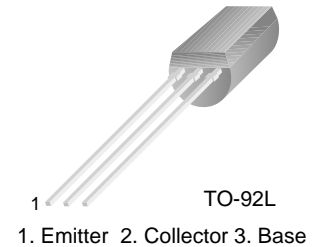


■■ APPLICATION: High Current Applications.

■■ MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	-80	V
Collector-emitter voltage	V_{CEO}	-75	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-2	A
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55~150	$^\circ\text{C}$


■■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	100		320		$V_{CE} = -2\text{ V}$, $I_C = -500\text{ mA}$
Collector Cut-off Current	I_{CBO}			-0.1	μA	$V_{CB} = -70\text{ V}$, $I_E = 0$
Emitter Cut-off Current	I_{EBO}			-0.1	μA	$V_{EB} = -5\text{ V}$, $I_C = 0$
Collector-Base Breakdown Voltage	BV_{CBO}	-80			V	$I_C = -0.1\text{ mA}$, $I_E = 0$
Collector-Emitter Breakdown Voltage	BV_{CEO}	-75			V	$I_C = -10\text{ mA}$, $I_B = 0$
Emitter-Base Breakdown Voltage	BV_{EBO}	-5			V	$I_E = -0.1\text{ mA}$, $I_C = 0$
Base-Emitter Voltage	V_{BE}			-1.0	V	$V_{CE} = -2\text{ V}$, $I_C = -500\text{ mA}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-2.0	V	$I_C = -1.5\text{ A}$, $I_B = -30\text{ mA}$
Gain bandwidth product	f_T		120		MHz	$I_C = -500\text{ mA}$, $V_{CE} = -2\text{ V}$
Common Base Output Capacitance	C_{ob}		48		PF	$V_{CB} = -10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$

■■ hFE Classification

Classification	O	Y
h_{FE}	100 ~ 200	160 ~ 320